

# 0.9V Drive Nch + Nch MOSFET

## EM6K34

### ● Structure

Silicon N-channel MOSFET

### ● Features

- 1) High speed switing.
- 2) Small package(EMT6).
- 3) Ultra low voltage drive(0.9V drive).

### ● Application

Switching

### ● Packaging specifications

Type	Package	Taping
	Code	T2R
	Basic ordering unit (pieces)	8000
EM6K34		○

### ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Limits	Unit
Drain-source voltage	V <sub>DSS</sub>	50	V
Gate-source voltage	V <sub>GSS</sub>	±8	V
Drain current	Continuous	I <sub>D</sub>	±200 mA
	Pulsed	I <sub>DP</sub> *1	±800 mA
Source current (Body Diode)	Continuous	I <sub>S</sub>	125 mA
	Pulsed	I <sub>SP</sub> *1	800 mA
Power dissipation	P <sub>D</sub> *2	150	mW / TOTAL
		120	mW / ELEMENT
Channel temperature	T <sub>ch</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C

\*1 P<sub>w</sub>≤10μs, Duty cycle≤1%

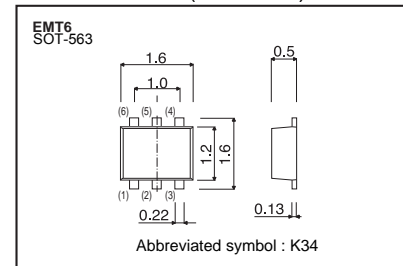
\*2 Each terminal mounted on a recommended land.

### ● Thermal resistance

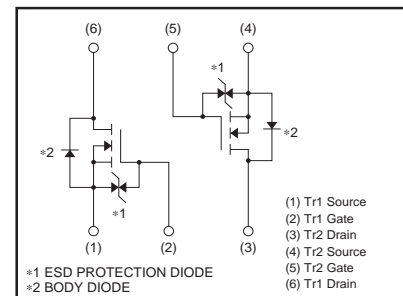
Parameter	Symbol	Limits	Unit
Channel to Ambient	R <sub>th</sub> (ch-a)*	833	°C/ W /TOTAL
		1042	°C/ W /ELEMENT

\* Each terminal mounted on a recommended land.

### ● Dimensions (Unit : mm)



### ● Inner circuit



● **Electrical characteristics** ( $T_a = 25^\circ\text{C}$ )

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	$\pm 10$	$\mu\text{A}$	$V_{GS}=\pm 8\text{V}$ , $V_{DS}=0\text{V}$
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	V	$I_D=1\text{mA}$ , $V_{GS}=0\text{V}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=50\text{V}$ , $V_{GS}=0\text{V}$
Gate threshold voltage	$V_{GS(th)}$	0.3	-	0.8	V	$V_{DS}=10\text{V}$ , $I_D=1\text{mA}$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	1.6	2.2	$\Omega$	$I_D=200\text{mA}$ , $V_{GS}=4.5\text{V}$
		-	1.7	2.4		$I_D=200\text{mA}$ , $V_{GS}=2.5\text{V}$
		-	2.0	2.8		$I_D=200\text{mA}$ , $V_{GS}=1.5\text{V}$
		-	2.2	3.3		$I_D=100\text{mA}$ , $V_{GS}=1.2\text{V}$
		-	3.0	9.0		$I_D=10\text{mA}$ , $V_{GS}=0.9\text{V}$
Forward transfer admittance	$ Y_{fs} ^*$	0.2	-	-	S	$I_D=200\text{mA}$ , $V_{DS}=10\text{V}$
Input capacitance	$C_{iss}$	-	26	-	pF	$V_{DS}=10\text{V}$
Output capacitance	$C_{oss}$	-	6	-	pF	$V_{GS}=0\text{V}$
Reverse transfer capacitance	$C_{rss}$	-	3	-	pF	$f=1\text{MHz}$
Turn-on delay time	$t_{d(on)}^*$	-	5	-	ns	$I_D=100\text{mA}$ , $V_{DD} \approx 25\text{V}$
Rise time	$t_r^*$	-	8	-	ns	$V_{GS}=4.5\text{V}$
Turn-off delay time	$t_{d(off)}^*$	-	17	-	ns	$R_L=250\Omega$
Fall time	$t_f^*$	-	43	-	ns	$R_G=10\Omega$

\*Pulsed

● **Body diode characteristics** (Source-Drain) ( $T_a = 25^\circ\text{C}$ )

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	$V_{SD}^*$	-	-	1.2	V	$I_S=200\text{mA}$ , $V_{GS}=0\text{V}$

\*Pulsed

● Electrical characteristics curves

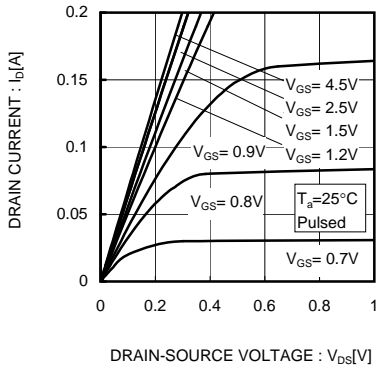


Fig.1 Typical Output Characteristics( I )

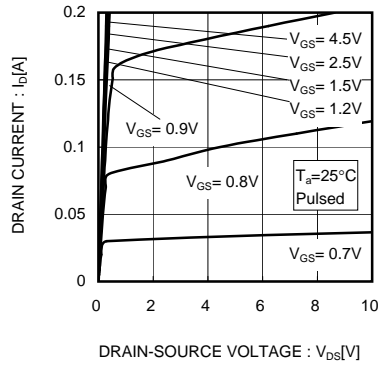


Fig.2 Typical Output Characteristics( II )

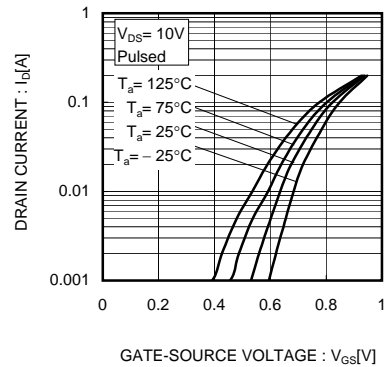


Fig.3 Typical Transfer Characteristics

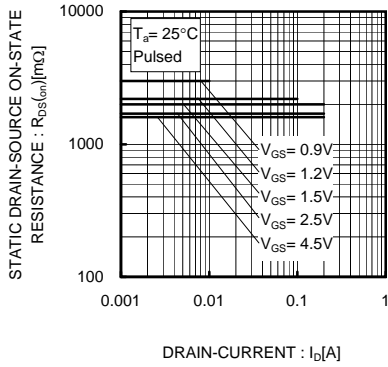


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current( I )

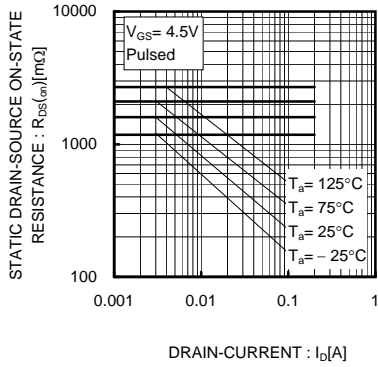


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current( II )

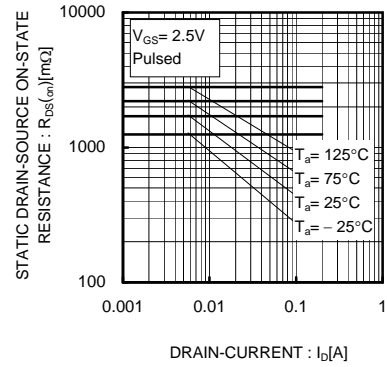


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current( III )

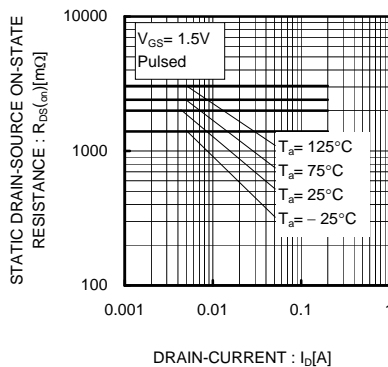


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current( IV )

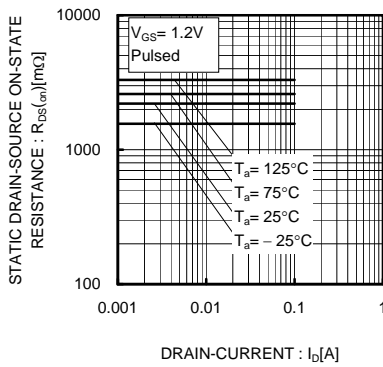


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current( V )

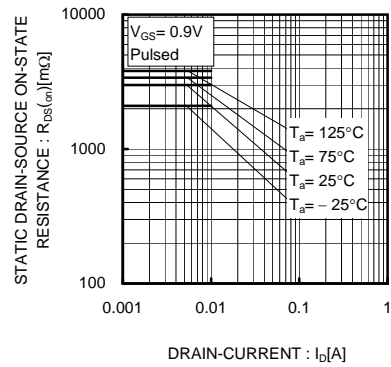


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current( VI )

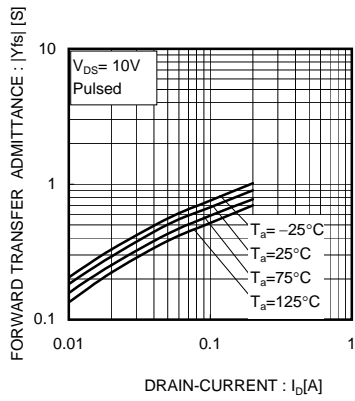


Fig.10 Forward Transfer Admittance vs. Drain Current

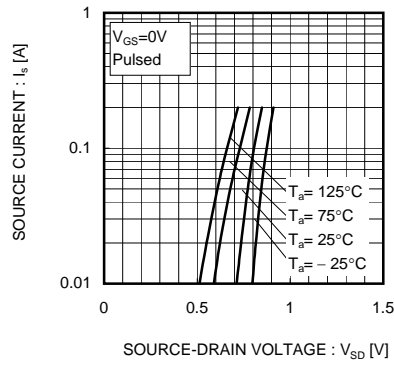


Fig.11 Reverse Drain Current vs. Source-Drain Voltage

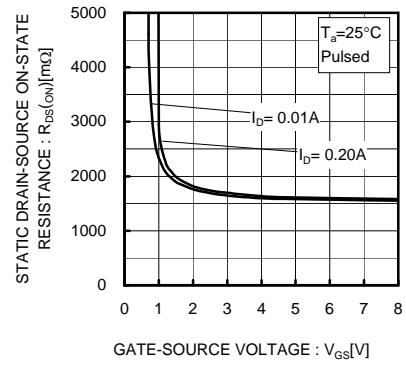


Fig.12 Static Drain-Source On-State Resistance vs. Gate Source Voltage

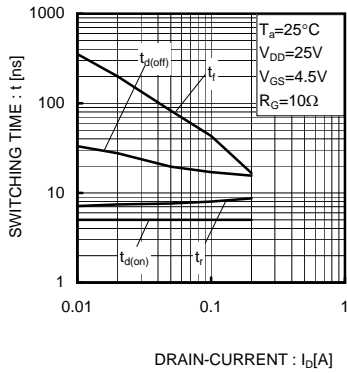


Fig.13 Switching Characteristics

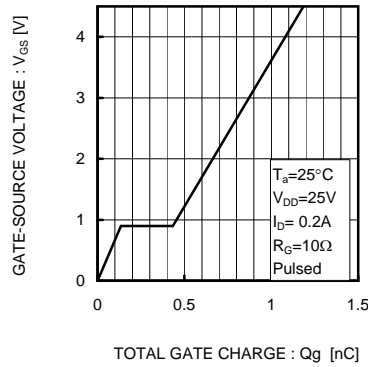


Fig.14 Typical Capacitance vs. Drain-Source Voltage

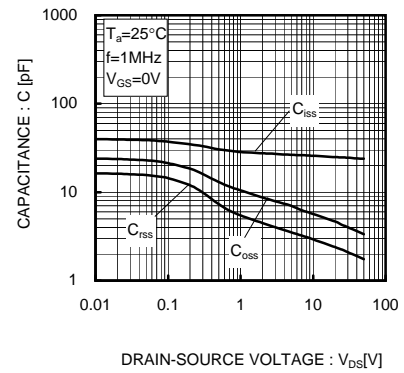


Fig.15 Typical Capacitance vs. Drain-Source Voltage

### ● Measurement circuits

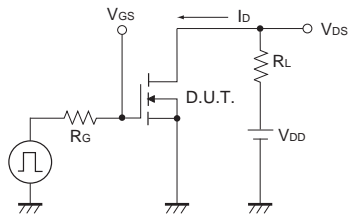


Fig.1-1 Switching time measurement circuit

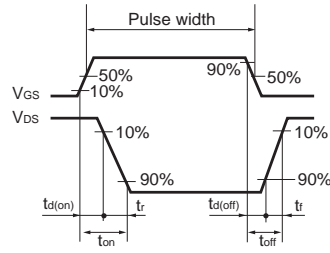


Fig.1-2 Switching waveforms

### ● Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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